

FPN430 FPN430A



PNP Low Saturation Transistor

These devices are designed for high current gain and low saturation voltage with collector currents up to 2.0 A continuous. Sourced from Process PB.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	35	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	2.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FPN430 / FPN430A	
P _D	Total Device Dissipation	1.0	W
R _{θJC}	Thermal Resistance, Junction to Case	50	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	125	°C/W

PNP Low Saturation Transistor
(continued)

FPN430 / FPN430A

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
--------	-----------	-----------------	-----	-----	-------

OFF CHARACTERISTICS

BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0	30		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA, I _E = 0	35		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA, I _C = 0	5.0		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 30 V, I _E = 0 V _{CB} = 30 V, I _E = 0, T _A = 100°C		100 10	nA μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4.0 V, I _C = 0		100	nA

ON CHARACTERISTICS*

h _{FE}	DC Current Gain	I _C = 100 mA, V _{CE} = 2.0 V I _C = 1.0 A, V _{CE} = 2.0 V I _C = 2.0 A, V _{CE} = 2.0 V	430 430A	100 250 60 40	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1.0 A, I _B = 100 mA I _C = 2.0 A, I _B = 200 mA	430 430A	500 450 800	mV mV mV
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1.0 A, I _B = 100 mA		1.25	V
V _{BE(on)}	Base-Emitter Saturation Voltage	I _C = 1.0 A, V _{CE} = 2.0 V		1.0	V

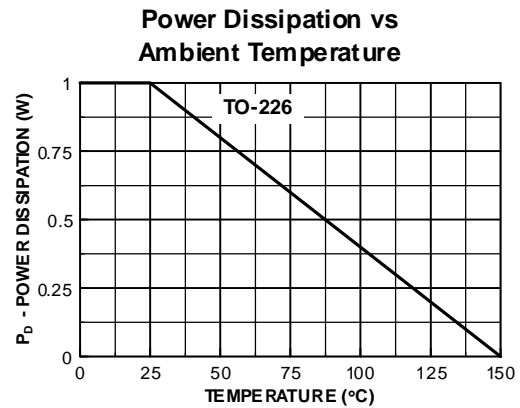
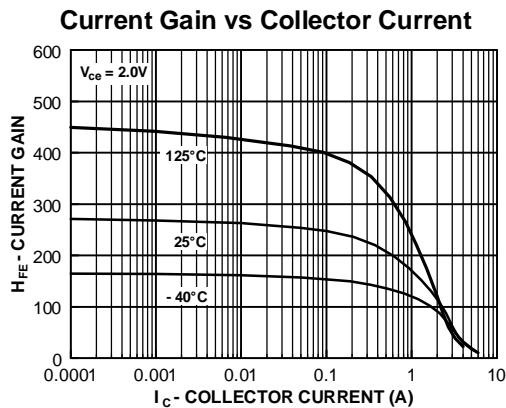
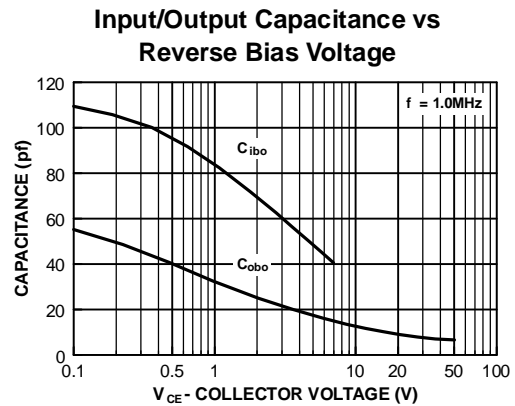
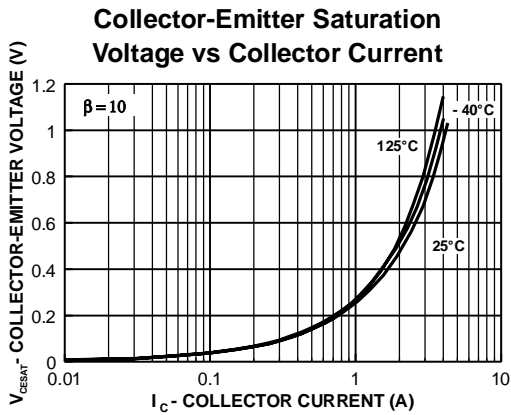
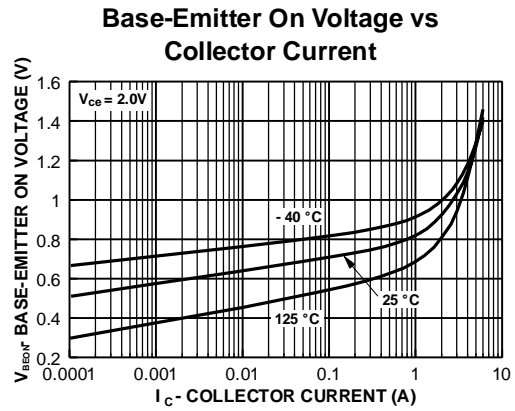
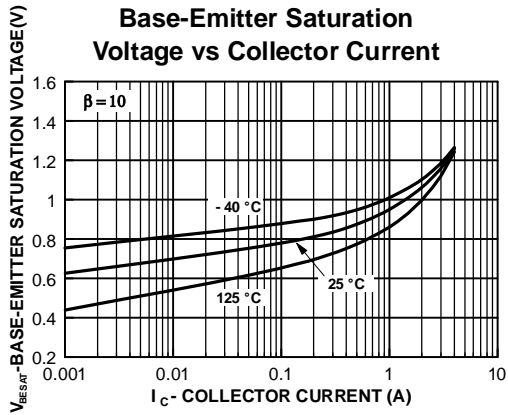
SMALL SIGNAL CHARACTERISTICS

C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz		25	pF
F _T	Transition Frequency	I _C = 100 mA, V _{CE} = 5.0 V, f = 100 MHz	100		MHz

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

Typical Characteristics



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FASTr™	PowerTrench®	SyncFET™
Bottomless™	GlobalOptoisolator™	QFET™	TinyLogic™
CoolFET™	GTO™	QS™	UHC™
CROSSVOLT™	HiSeC™	QT Optoelectronics™	VCX™
DOME™	ISOPLANAR™	Quiet Series™	
E ² CMOS™	MICROWIRE™	SILENT SWITCHER®	
EnSigna™	OPTOLOGIC™	SMART START™	
FACT™	OPTOPLANAR™	SuperSOT™-3	
FACT Quiet Series™	PACMAN™	SuperSOT™-6	
FAST®	POP™	SuperSOT™-8	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.